BLM7G1822S-20PB; BLM7G1822S-20PBG LDMOS 2-stage power MMIC

AMPLEON

Rev. 4 — 1 September 2015

Product data sheet

Product profile

1.1 General description

The BLM7G1822S-20PB(G) is a dual section, 2-stage power MMIC using Ampleon's state of the art GEN7 LDMOS technology. This multiband device is perfectly suited as general purpose driver or small cell final in the frequency range from 1805 MHz to 2170 MHz. Available in gull wing or straight lead outline.

Table 1. **Performance**

Typical RF performance at $T_{case} = 25$ °C; $I_{Dq1} = 27$ mA; $I_{Dq2} = 76$ mA. Test signal: 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01% probability on CCDF; per section unless otherwise specified in a class-AB production circuit.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	η_{D}	ACPR _{5M}
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
single carrier W-CDMA	2167.5	28	2	32.3	23	-41

1.2 Features and benefits

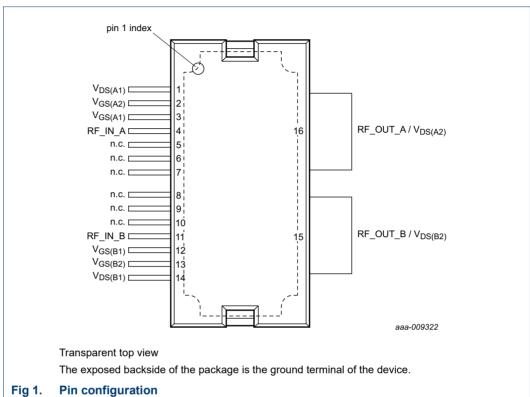
- Designed for broadband operation (frequency 1805 MHz to 2170 MHz)
- High section-to-section isolation enabling multiple combinations
- Integrated temperature compensated bias
- Biasing of individual stages is externally accessible
- Integrated ESD protection
- Excellent thermal stability
- High power gain
- On-chip matching for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

- RF power MMIC for multi-carrier and multi-standard GSM, W-CDMA and LTE base stations in the 1805 MHz to 2170 MHz frequency range. Possible circuit topologies are the following as also depicted in Section 8.1:
 - Dual section or single ended
 - Doherty
 - Quadrature combined
 - Push-pull

Pinning information 2.

Pinning 2.1



2.2 Pin description

Pin description Table 2.

Symbol	Pin	Description
V _{DS(A1)}	1	drain-source voltage of driver stage A1
V _{GS(A2)}	2	gate-source voltage of final stage A2
V _{GS(A1)}	3	gate-source voltage of driver stage A1
RF_IN_A	4	RF input section A
n.c.	5	not connected
n.c.	6	not connected
n.c.	7	not connected
n.c.	8	not connected
n.c.	9	not connected
n.c.	10	not connected
RF_IN_B	11	RF input section B
V _{GS(B1)}	12	gate-source voltage of driver stage B1
V _{GS(B2)}	13	gate-source voltage of final stage B2
V _{DS(B1)}	14	drain-source voltage of driver stage B1

Table 2. Pin description ... continued

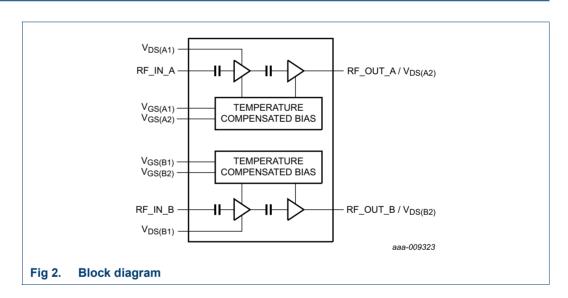
Symbol	Pin	Description
RF_OUT_B/V _{DS(B2)}	15	RF output section B / drain-source voltage of final stage B2
RF_OUT_A/V _{DS(A2)}	16	RF output section A / drain-source voltage of final stage A2
GND	flange	RF ground

3. Ordering information

Table 3. Ordering information

Type number	Package	Package						
	Name	Description	Version					
BLM7G1822S-20PB	HSOP16F	plastic, heatsink small outline package; 16 leads(flat)	SOT1211-2					
BLM7G1822S-20PBG	HSOP16	plastic, heatsink small outline package; 16 leads	SOT1212-2					

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C
T _{case}	case temperature		-	150	°C

^[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

Measured for total device.

Symbol	Parameter	Conditions	Value	Unit
R _{th(j-c)}	thermal resistance from junction to case	final stage; $T_{case} = 90 ^{\circ}\text{C}$; $P_L = 3.56 \text{W}$	1.9	K/W
		driver stage; $T_{case} = 90 \text{ °C}$; $P_L = 3.56 \text{ W}$	6.2	K/W

^[1] When operated with a CW signal.

7. Characteristics

Table 6. DC characteristics

 $T_{\text{case}} = 25 \, ^{\circ}\text{C}$; per section unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Final stag	e				<u> </u>		
V _{(BR)DSS}	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 150.8 μA		65	-	-	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 76 \text{ mA}$		1.5	2	2.5	V
		V _{DS} = 28 V; I _D = 76 mA	<u>[1]</u>	1.7	2.65	3.6	V
ΔI _{Dq} /ΔT	quiescent drain current variation with temperature	-40 °C ≤ T _{case} ≤ +85 °C	[1]	-	±1	-	%
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V		-	-	1.4	μΑ
I _{DSX}	drain cut-off current	V _{GS} = 5.55 V; V _{DS} = 10 V		-	2.8	-	Α
I _{GSS}	gate leakage current	V _{GS} = 1.0 V; V _{DS} = 0 V		-	-	140	nA
Driver sta	ge	-			,	'	'
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 30.16 \mu\text{A}$		65	-	-	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 27 \text{ mA}$		1.6	2.1	2.6	V
		V _{DS} = 28 V; I _D = 27 mA	[2]	1.9	2.85	3.8	V
ΔI _{Dq} /ΔT	quiescent drain current variation with temperature	-40 °C ≤ T _{case} ≤ +85 °C	[2]	-	±1	-	%
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V		-	-	1.4	μΑ
I _{DSX}	drain cut-off current	V _{GS} = 5.55 V; V _{DS} = 10 V		-	0.55	-	Α
I _{GSS}	gate leakage current	V _{GS} = 1.0 V; V _{DS} = 0 V		-	-	140	nA

^[1] In production circuit with 1105 Ω gate feed resistor.

^[2] In production circuit with 765 Ω gate feed resistor.

Table 7. RF Characteristics

Typical RF performance at $T_{\rm case} = 25$ °C; $V_{\rm DS} = 28$ V; $I_{\rm Dq1} = 27$ mA; $I_{\rm Dq2} = 76$ mA; $P_{\rm L(AV)} = 2$ W. Per section unless otherwise specified, measured in an Ampleon wideband f = 1807.5 MHz to 2167.5 MHz straight lead production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Test signa	II: single carrier W-CDMA [1]	,	'			
Gp	power gain	f = 1807.5 MHz	-	34	-	dB
		f = 2167.5 MHz	30.8	32.3	33.8	dB
η _D	drain efficiency	f = 1807.5 MHz	-	22	-	%
		f = 2167.5 MHz	20	23	-	%
RLin	input return loss	f = 2167.5 MHz	-	-19	-10	dB
ACPR _{5M}	adjacent channel power ratio (5 MHz)	f = 1807.5 MHz	-	-41	-	dBc
		f = 2167.5 MHz	-	-41	-37	dBc
PARO	output peak-to-average ratio	f = 1807.5 MHz	-	8.4	-	dB
		f = 2167.5 MHz	7.2	8.4	-	dB
$\Delta I_{Dq}/\Delta T$	quiescent drain current variation with	T = -40 °C to +85 °C				
	temperature	final stage I_{Dq} ; gate feed resistor = 1105 Ω	-	±1	-	%
		driver stage I_{Dq} ; gate feed resistor = 765 Ω	-	±1	-	%
Test signa	I: CW [2]		,	,		_
$\Delta \phi_{s21}$	phase response difference	between sections	-10	-	+10	deg
$\Delta s_{21} ^2$	insertion power gain difference	between sections	-0.5	-	+0.5	dB

^{[1] 3}GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01% probability on CCDF.

8. Application information

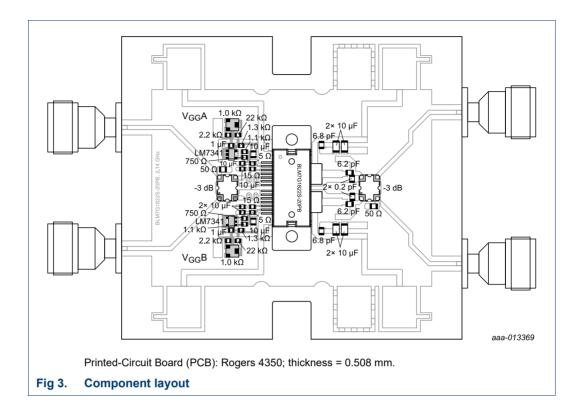
Table 8. Typical performance

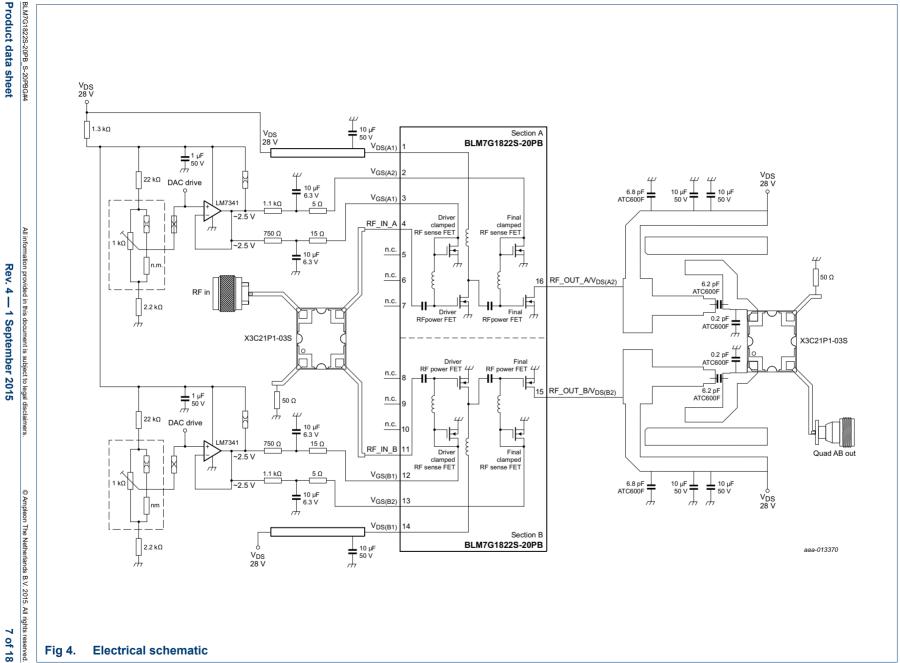
Test signal: 1-tone CW; RF performance at $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq1} = 45$ mA (both sections); $I_{Dq2} = 140$ mA (both sections) unless otherwise specified, measured in an Ampleon f = 2110 MHz to 2170 MHz straight lead class AB application circuit (see Figure 3 for the component layout and Figure 4 for the electrical schematic).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P _{L(1dB)}	output power at 1 dB gain compression	f = 2140 MHz	-	43.5	-	W
P _{L(3dB)}	output power at 3 dB gain compression	f = 2140 MHz	-	44.1	-	W
η_{D}	drain efficiency	at P _{L(1dB)} ; f = 2140 MHz	-	47.6	-	%
Gp	power gain	P _{L(AV)} = 1.585 W; f = 2140 MHz	-	31.5	-	dB
B _{video}	video bandwidth	2-tone CW; P _{L(AV)} = 1.585 W; f = 2140 MHz	-	170	-	MHz
G _{flat}	gain flatness	over a frequency range of 60 MHz; P _{L(AV)} = 1.585 W	-	0.4	-	dB
ΔG/ΔΤ	gain variation with temperature	f = 2140 MHz	-	0.03	-	dB/°C
$ s_{12} ^2$	isolation	between sections A and B; P _{L(AV)} = 1.585 W; f = 2140 MHz	-	28.5	-	dB
K	Rollett stability factor	T = -40 °C; f = 0.1 GHz to 3 GHz	-	>1	-	

^[1] Measured on dual section evaluation board $I_{Dq1} = 40$ mA (both sections); $I_{Dq2} = 150$ mA (both sections).

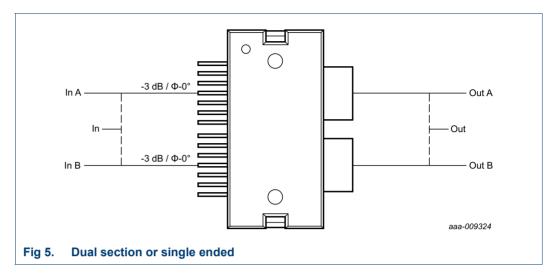
^[2] f = 2170 MHz.

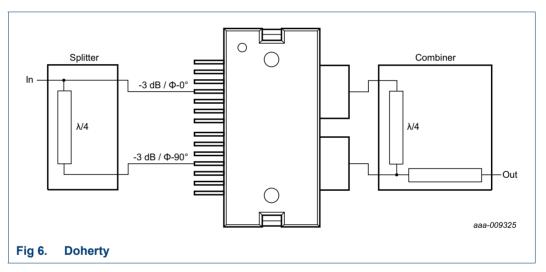


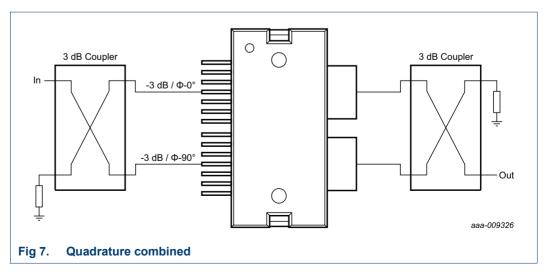


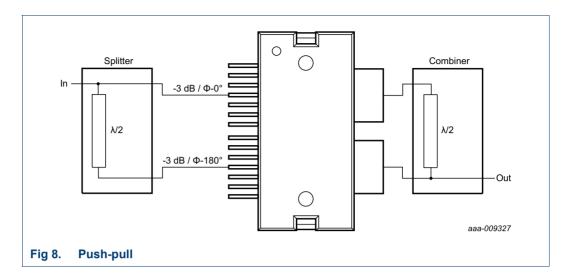
BLM7G1822S-20PB(G) LDMOS 2-stage power MMIC

8.1 Possible circuit topologies









8.2 Ruggedness in class-AB operation

The BLM7G1822S-20PB and BLM7G1822S-20PBG are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq1} = 20 mA (per section); I_{Dq2} = 75 mA (per section); P_i = 16 dBm (CW and corresponding to $P_{L(3dB)}$ under Z_S = 50 Ω load); f = 2140 MHz.

8.3 Impedance information

Table 9. Typical impedance at 3 dB compression point

Measured load-pull data per section; test signal: pulsed CW; $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq1} = 20$ mA; $I_{Dq2} = 65$ mA; $I_{Dq2} = 65$ mA; $I_{Dq2} = 65$ mA; $I_{Dq3} = 10$ %; $I_{Dq3} = 10$ %

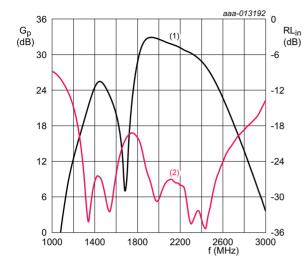
	tuned for maximum output power						tuned for maximum efficiency					
f	Z _L	G _{p(max)}	PL	η _{add}	AM-PM conversion	Z _L	G _{p(max)}	PL	η _{add}	AM-PM conversion		
(MHz)	(Ω)	(dB)	(W)	(%)	(deg)	(Ω)	(dB)	(W)	(%)	(deg)		
BLM7G1	1822S-20PB											
1700	15.3 – j14.5	33.2	42.7	50.6	8.3	28.5 – j20.2	34.6	41.6	56.5	9.2		
1800	16.3 – j11.7	32.9	42.7	50.8	6.3	31.3 – j8.60	34.1	41.6	57.1	7.0		
1900	16.1 – j9.70	32.1	42.8	50.8	6.1	26.5 – j0.01	33.3	41.7	57.3	6.9		
2000	15.5 – j8.10	31.5	42.8	50.1	6.1	21.0 + j2.20	32.6	42.0	56.4	7.3		
2100	14.4 – j6.90	31.5	42.9	50.0	6.9	15.6 + j2.00	32.9	42.1	55.8	8.6		
2200	13.7 – j6.60	31.7	42.7	49.8	8.5	12.3 + j1.20	33.0	41.6	54.3	9.6		
2300	12.8 – j6.80	31.4	42.5	49.1	10.6	10.0 + j0.10	32.5	41.3	53.6	10.3		
BLM7G1	1822S-20PBG	·										
1700	15.8 – j16.1	33.5	42.5	52.9	9.2	28.9 – j21.8	35.1	41.6	57.9	11.1		
1800	16.5 – j13.8	32.9	42.5	51.2	7.7	30.6 – j11.6	34.2	41.6	56.8	8.4		
1900	16.7 – j12.4	32.2	42.5	50.2	7.2	27.9 – j4.64	33.5	41.7	55.9	7.8		
2000	16.3 – j9.74	31.7	42.5	51.2	7.3	20.4 + j0.45	32.7	41.7	55.6	9.0		
2100	15.6 – j8.61	31.5	42.6	52.0	9.5	15.9 + j0.68	32.6	41.7	56.5	11.8		
2200	14.6 – j8.87	31.3	42.5	49.7	10.3	12.7 – j0.44	32.4	41.6	53.8	12.1		
2300	13.4 – j9.32	30.5	42.4	48.2	12.8	10.7 – j1.98	31.7	41.6	53.7	13.2		

BLM7G1822S-20PB_S-20PBG#4

All information provided in this document is subject to legal disclaimers.

© Ampleon The Netherlands B.V. 2015. All rights reserved.

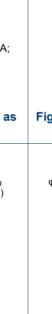
8.4 Graphs

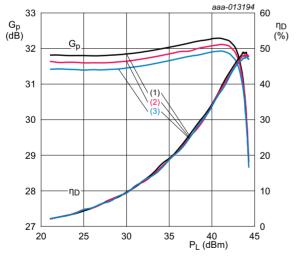


 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 22 mA; I_{Dq2} = 70 mA; P_I = 1.585 W. Per section.

- (1) magnitude of G_p
- (2) magnitude of RLin

Fig 9. Wideband power gain and input return loss as function of frequency; typical values

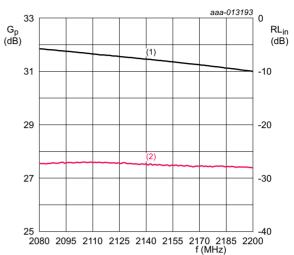




 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 22 mA; I_{Dq2} = 70 mA. Per section.

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

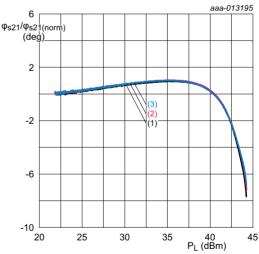
Fig 11. Power gain and drain efficiency as function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 22 mA; I_{Dq2} = 70 mA; P_L = 1.585 W. Per section.

- (1) magnitude of G_p
- (2) magnitude of RLin

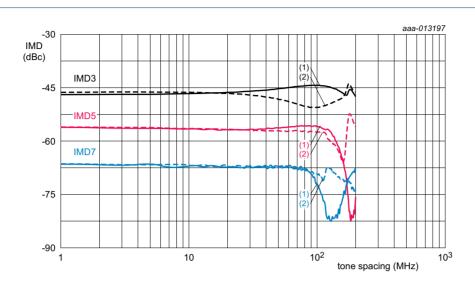
Fig 10. In-band power gain and input return loss as function of frequency; typical values



Normalized at P_L = 22 dBm; T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 22 mA; I_{Dq2} = 70 mA. Per section.

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

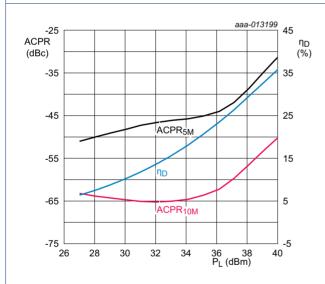
Fig 12. Normalized phase response as a function of output power; typical values



 $T_{case} = 25 \, ^{\circ}\text{C}; V_{DS} = 28 \, \text{V}; I_{Dq1} = 22 \, \text{mA}; I_{Dq2} = 70 \, \text{mA}; f = 2140 \, \text{MHz}; 2-tone CW; P_{L(AV)} = 0.25 \, \text{W}. Per section.$

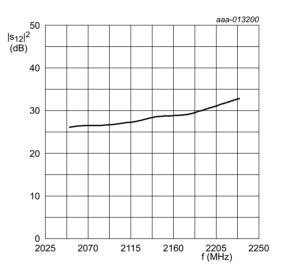
- (1) IMD low
- (2) IMD high

Fig 13. Intermodulation distortion as a function of tone spacing; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 22 mA; I_{Dq2} = 70 mA; f = 2140 MHz; 1-carrier W-CDMA; test model 1; PAR = 7.2 dB at 0.01 % probability on CCDF. Per section.

Fig 14. Adjacent channel power ratio and drain efficiency as function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 20 mA; I_{Dq2} = 75 mA. Per section. Measured on evaluation board.

Fig 15. Isolation as a function of frequency; typical values

9. Package outline

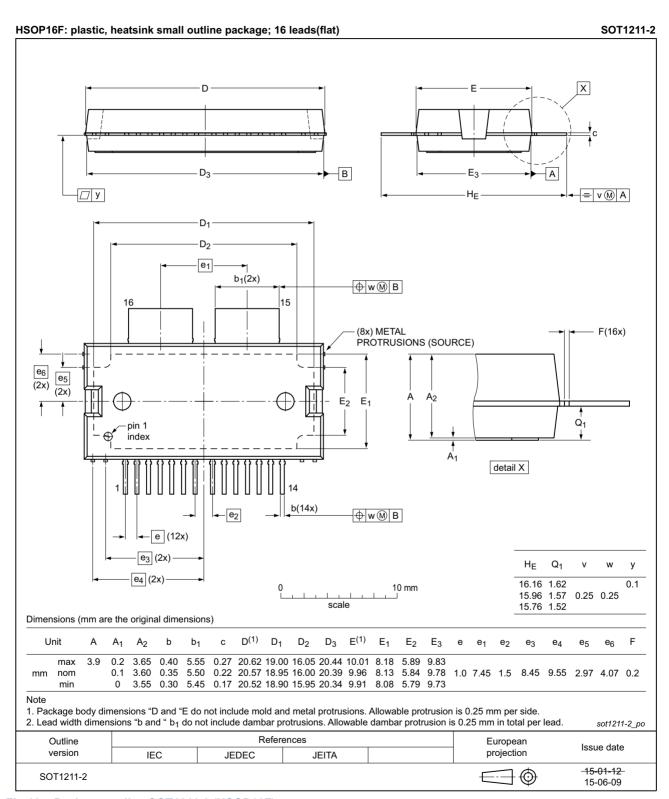


Fig 16. Package outline SOT1211-2 (HSOP16F)

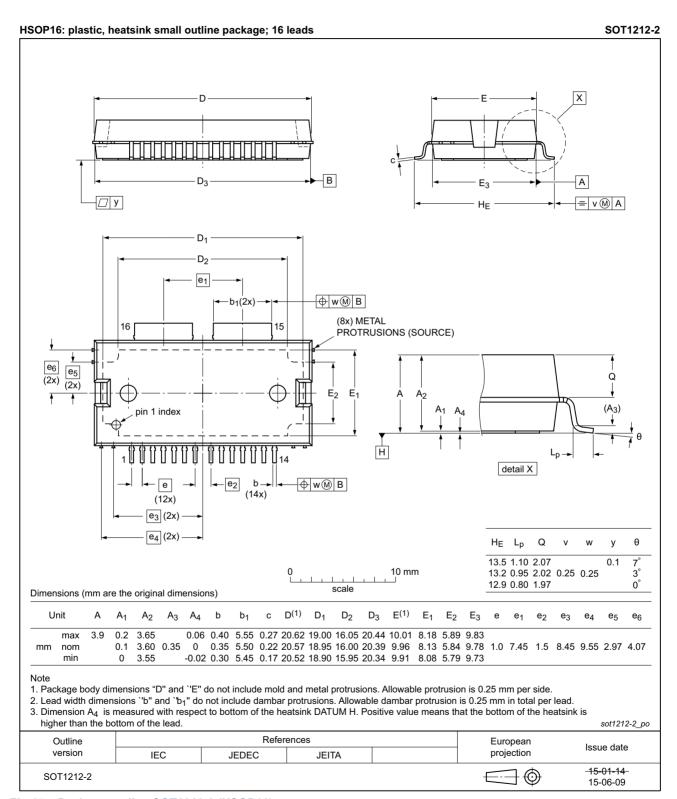


Fig 17. Package outline SOT1212-2 (HSOP16)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

11. Abbreviations

Table 10. Abbreviations

Acronym	Description
AM	Amplitude Modulation
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
GEN7	Seventh Generation
GSM	Global System for Mobile Communications
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LTE	Long Term Evolution
MMIC	Monolithic Microwave Integrated Circuit
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
PM	Phase Modulation
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

12. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLM7G1822S-20PB_S-20PBG#4	20150901	Product data sheet		BLM7G1822S-20PB_S -20PBG v.3
Modifications:		t of this document has bee	en redesigned to co	omply with the new
	 Legal texts 	s have been adapted to the	e new company na	me where appropriate.
BLM7G1822S-20PB_S-20PBG v.3	20150701	Product data sheet	-	BLM7G1822S-20PB_ S-20PBG v.2
BLM7G1822S-20PB_S-20PBG v.2	20140626	Objective data sheet	-	BLM7G1822S-20PB_ S-20PBG v.1
BLM7G1822S-20PB_S-20PBG v.1	20131219	Objective data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Ampleon does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Ampleon sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Ampleon and its customer, unless Ampleon and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Ampleon product is deemed to offer functions and qualities beyond those described in the Product data sheet.

13.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Ampleon does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Ampleon takes no responsibility for the content in this document if provided by an information source outside of Ampleon.

In no event shall Ampleon be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Ampleon' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Ampleon.

Right to make changes — Ampleon reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Ampleon products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an

Ampleon product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Ampleon and its suppliers accept no liability for inclusion and/or use of Ampleon products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Ampleon makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Ampleon products, and Ampleon accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Ampleon product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Ampleon does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Ampleon products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Ampleon does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Ampleon products are sold subject to the general terms and conditions of commercial sale, as published at http://www.ampleon.com/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Ampleon hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Ampleon products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

BLM7G1822S-20PB S-20PBG#4

All information provided in this document is subject to legal disclaimers.

© Ampleon The Netherlands B.V. 2015. All rights reserved.

BLM7G1822S-20PB(G)

LDMOS 2-stage power MMIC

Non-automotive qualified products — Unless this data sheet expressly states that this specific Ampleon product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Ampleon accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Ampleon' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Ampleon' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Ampleon for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Ampleon' standard warranty and Ampleon' product specifications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

Any reference or use of any 'NXP' trademark in this document or in or on the surface of Ampleon products does not result in any claim, liability or entitlement vis-à-vis the owner of this trademark. Ampleon is no longer part of the NXP group of companies and any reference to or use of the 'NXP' trademarks will be replaced by reference to or use of Ampleon's own Any reference or use of any 'NXP' trademark in this document or in or on the surface of Ampleon products does not result in any claim, liability or entitlement vis-à-vis the owner of this trademark. Ampleon is no longer part of the NXP group of companies and any reference to or use of the 'NXP' trademarks will be replaced by reference to or use of Ampleon's own trademarks

14. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

AMPLEON

BLM7G1822S-20PB(G)

LDMOS 2-stage power MMIC

15. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
2	Pinning information 2
2.1	Pinning
2.2	Pin description
3	Ordering information 3
4	Block diagram 3
5	Limiting values
6	Thermal characteristics
7	Characteristics4
8	Application information 5
8.1	Possible circuit topologies 8
8.2	Ruggedness in class-AB operation 9
8.3	Impedance information
8.4	Graphs
9	Package outline
10	Handling information 14
11	Abbreviations14
12	Revision history
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks17
14	Contact information 17
15	Contents 19

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.